

Part Number: ILD0814CW60 (Preliminary)

Integra

TECHNOLOGIES, INC.

60W Broadband RF Power LDMOS FET

The high power transistor part number ILD0814CW60 is designed for the frequency band 850-1450 MHz. Operating at CW conditions this LDMOS FET device supplies a minimum of 60 watts of power across the instantaneous operating bandwidth of 850-1450 MHz. All devices are 100% screened for large signal RF parameters.



Silicon LDMOS FET

- High Power Gain
- Superior thermal stability

Class AB Operation

- Gate biased to $I_{DQ} = 250 \text{ mA}$

Configuration

- Common Source

Gold Metal

- Maximum Reliability

Package

- Thermally enhanced
- Pb-free and RoHS-compliant

Epoxy Sealed Lid

- Gross Leak Qualified

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

General Information ILD0814CW60	Test Sequence Name	Freq (MHz)	PIN (W)	RL (dB)	POUT (W)	GP (dB)	Gf (dB)	Id (A)	nd (%)	VSWR-LMT 1.5:1 (P-F)	VSWR-LMT 3:1 (P-F)
Date: 5/13/2009											
Assbly Lot - SN : 50012372-10	Nominal	850	5.0	-12.3	102.0	13.10	--	5.631	60.4	P	
Wafer : NA											
Test Fixture : NA	Nominal	950	5.0	-17.5	85.0	12.30		5.866	48.3	P	
Pass / Fail : Device Passes											
OPERATOR: FB	Nominal	1050	5.0	-14.5	86.0	12.36	--	5.303	54.1	P	
Conditions: CW											
Vd=30V	Nominal	1150	5.0	-18.0	84.0	12.25	1.83	4.817	58.1	P	
Idq=250mA											
	Nominal	1250	5.0	-18.0	78.0	11.93	--	4.368	59.5		P
	Nominal	1350	5.0	-14.4	75.0	11.76	--	3.809	65.6		P
	Nominal	1450	5.0	-18.0	67.0	11.27	--	3.533	63.2		P

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	V_{DSS}	--	65	V	--
BD	Gate-Source Voltage	V_{GS}	-0.5	12	V	--
BD	Storage Temperature Range	T_{STG}	-40	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	1.25	°C/W	$V_{DS}=30V, I_{DQ}=250mA, T_F=25\pm 5^\circ C, P_{IN}=5W, CW, F=F1, F2, F3, F4, F5, F6, F7.$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	BV_{DSS}	65		V	$I_D = 10\mu A, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Drain Leakage Current	I_{DSS}		1	μA	$V_{DS} = 30V, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Gate Threshold Voltage	V_{GSTH}	2	4	V	$I_{DQ} = 250mA, V_{DS} = 30V, T_F = 25\pm 5^\circ C$

RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	RL	-18	-10	dB	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4, F5, F6, F7.$
100%	Power Gain	G_p	10.8	13.3	dB	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4, F5, F6, F7.$
100%	Output Power	P_o	60	107	W	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4, F5, F6, F7.$
100%	Drain Efficiency in Lower Band	η_{dA}	42	80	%	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4.$
100%	Drain Efficiency in Higher Band	η_{dB}	50	80	%	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F5, F6, F7$
100%	Load Mismatch Tolerance In Power Band	LMTA	1.5:1	--	--	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4$ Rotate 1.5:1 output VSWR through 360° phase. Survival.
100%	Load Mismatch Tolerance	LMTB	3:1	--	--	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F5, F6, F7.$ Rotate 3:1 output VSWR through 360° phase. Survival.
100%	Gain Flatness	dG	--	2.5	dB	$V_d=30V, P_{IN} = 5W, CW, I_{dq}=250mA, T_F=25\pm 5^\circ C, F=F1, F2, F3, F4, F5, F6, F7.$
Note 1	F1= 850 MHz, F2= 950 MHz, F3= 1050 MHz, F4= 1150 MHz, F5= 1250 MHz, F6= 1350 MHz, F7= 1450 MHz.					
Note 2	T_F = Device flange temperature.					
Note 3	Screen 'BD' = parameter qualified By Design.					

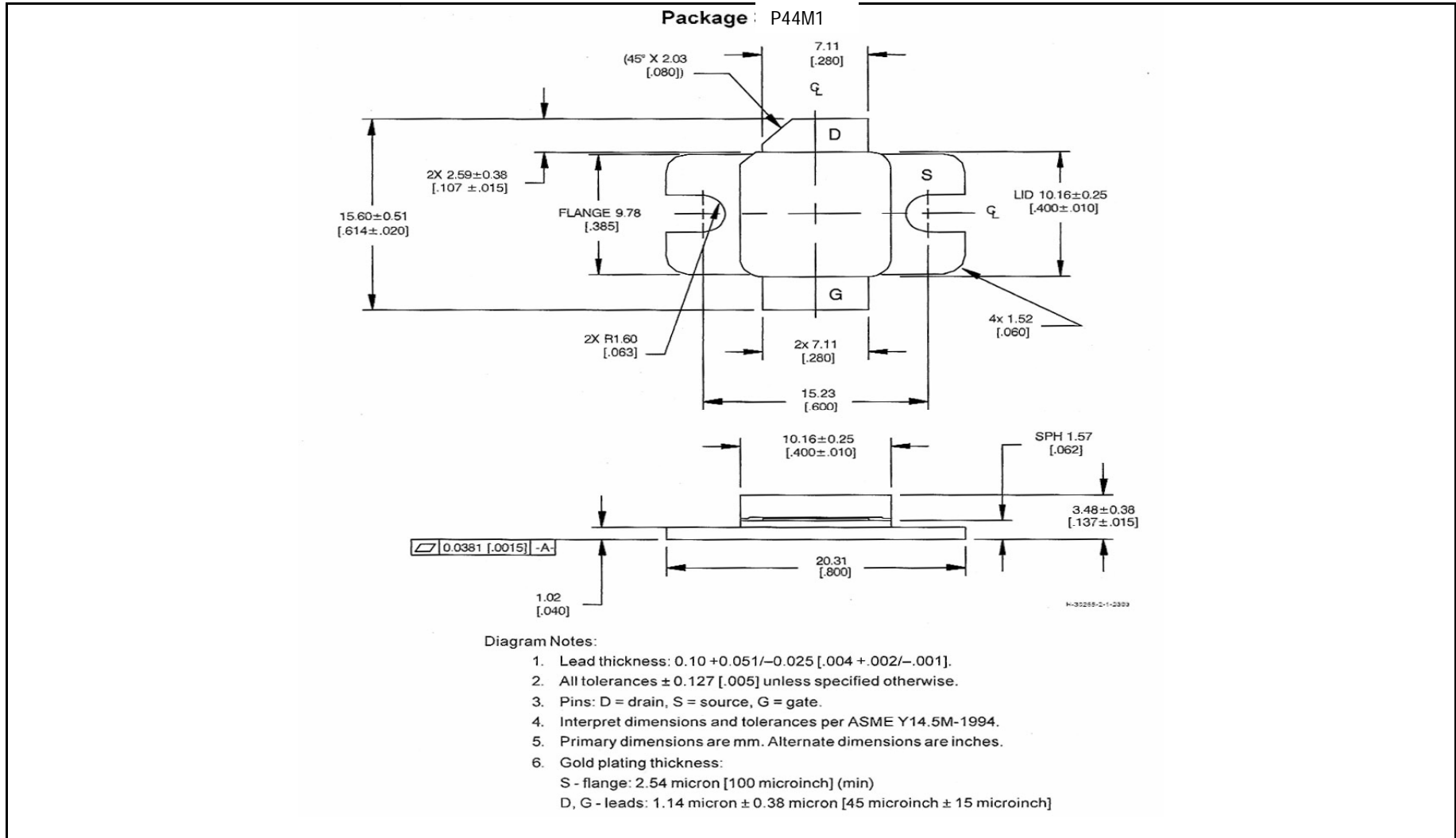
RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

Frequency (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
850	2.02 - j1.59	3.57 - j3.59
950	2.25 - j0.82	3.64 - j2.57
1050	2.61 - j0.35	3.83 - j1.81
1150	2.89 - j0.25	4.00 - j1.32
1250	2.77 - j0.40	4.06 - j1.07
1350	2.21 - j0.36	3.88 - j0.94
1450	1.60 + j0.11	3.49 - j0.70

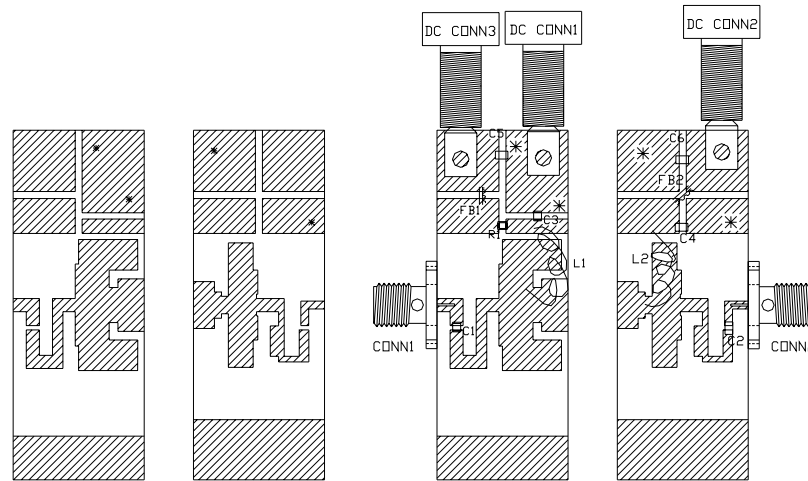
50 Ω hm

50 Ω hm

PACKAGE DIMENSIONAL OUTLINE DRAWING

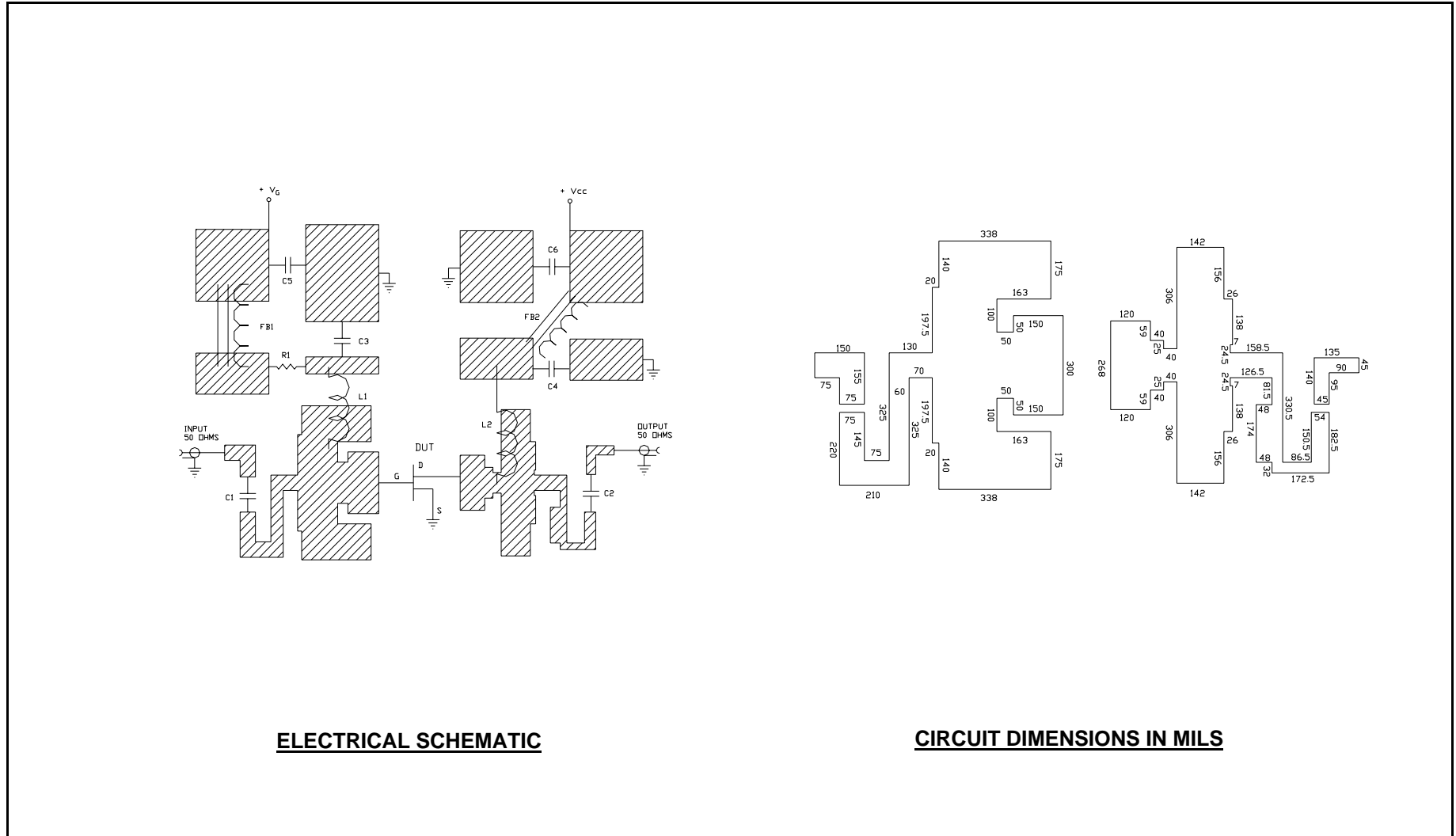


RF TEST FIXTURE



COMPONENT	DESCRIPTION
DUT	TRANSISTOR #ILD0814CW60, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS RT6010.2LM 1oz. Cu BOTH SIDES
C1, C2, C3, C4	CHIP CAPACITOR, 33 pF
C5	CHIP CAPACITOR, 3300 pF
C6	CHIP CAPACITOR, 1uF
GS	GROUND SHIM, COPPER, TH=0.001" *
CONN1, CONN2	SMA CONNECTOR, TYPE QS #2052-5636-02
INPUT PC BOARD CARRIER	2 INCH BRASS - 02
OUTPUT PC BOARD CARRIER	2 INCH BRASS - 02
TRANSISTOR CARRIER	2 INCH COPPER - 15
TRANSISTOR CLAMP	NORYL CLAMP -15
HEATSINK	2 INCH HEATSINK - 11
DC CONN1	BANANA JACK, BLACK
DC CONN2	BANANA JACK, RED
DC CONN3	BANANA JACK, BLUE
FBI, FB2	FERRITE BEAD
R1	CHIP RESISTOR, 10 ohms
L1, L2	INDUCTOR, 6 TURNS, WIRE# 22, ID= 0.100"
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

RF TEST FIXTURE



DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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